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NOTICE OF ALLOWANCE AND FEE(S) DUE

33804

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02/10/2004

SUPREME PATENT SERVICES POST OFFICE BOX 2339 SARATOGA, CA 95070 EXAMINER .

RAMSEY, KENNETH J

ART UNIT PAPER NUMBER

DATE MAILED: 02/10/2004

2879

APPLICATION NO.	FILING DATE	. FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/072,965	02/09/2002	Hua-Chi Cheng	02117-URLX	2257

TITLE OF INVENTION: CATHODE PLATE OF A CARBON NANO TUBE FIELD EMISSION DISPLAY AND ITS FABRICATION METHOD

APPLN. TYPE	SMALL ENTITY	ISSUE FEE	PUBLICATION FEE	TOTAL FEE(S) DUE	DATE DUE
nonprovisional	NO	\$1330	\$300	\$1630	05/10/2004

THE APPLICATION IDENTIFIED ABOVE HAS BEEN EXAMINED AND IS ALLOWED FOR ISSUANCE AS A PATENT. PROSECUTION ON THE MERITS IS CLOSED. THIS NOTICE OF ALLOWANCE IS NOT A GRANT OF PATENT RIGHTS. THIS APPLICATION IS SUBJECT TO WITHDRAWAL FROM ISSUE AT THE INITIATIVE OF THE OFFICE OR UPON PETITION BY THE APPLICANT. SEE 37 CFR 1.313 AND MPEP 1308.

THE ISSUE FEE AND PUBLICATION FEE (IF REQUIRED) MUST BE PAID WITHIN THREE MONTHS FROM THE MAILING DATE OF THIS NOTICE OR THIS APPLICATION SHALL BE REGARDED AS ABANDONED. THIS STATUTORY PERIOD CANNOT BE EXTENDED. SEE 35 U.S.C. 151. THE ISSUE FEE DUE INDICATED ABOVE REFLECTS A CREDIT FOR ANY PREVIOUSLY PAID ISSUE FEE APPLIED IN THIS APPLICATION. THE PTOL-85B (OR AN EQUIVALENT) MUST BE RETURNED WITHIN THIS PERIOD EVEN IF NO FEE IS DUE OR THE APPLICATION WILL BE REGARDED AS ABANDONED.

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- III. All communications regarding this application must give the application number. Please direct all communications prior to issuance to Mail Stop ISSUE FEE unless advised to the contrary.

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This collection of information of the property	ation is required by 37 CFR by the public which is to fit yis governed by 35 U.S.C. I stress to complete, including garm to the USPTO. Time will the amount of time you re this burden, should be sent to Office, U.S. Department of SEND FEES OR COMPLET for Patents, Alexandria, Virgeduction Act of 1995, no publics it displays a valid OME.	1.311. The informale (and by the USF 22 and 37 CFR 1.14 athering, preparing, Il vary depending u equire to complete to the Chief Inform of Commerce, AloTED FORMS TO ginia 22313-1450.	ation is required TO to process) 4. This collection and submitting to the individuation officer, U exandria, Virgin THIS ADDRES d to respond to the top to the top to the top to the top the t	to an is he al or S. ia S		·



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SUPREME PATENT SERVICES POST OFFICE BOX 2339		RAMSEY, KENNETH J			
SARATOGA,				ART UNIT	PAPER NUMBER
				2879	
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Determination of Patent Term Adjustment under 35 U.S.C. 154 (b)

(application filed on or after May 29, 2000)

The Patent Term Adjustment to date is 181 day(s). If the issue fee is paid on the date that is three months after the mailing date of this notice and the patent issues on the Tuesday before the date that is 28 weeks (six and a half months) after the mailing date of this notice, the Patent Term Adjustment will be 181 day(s).

If a Continued Prosecution Application (CPA) was filed in the above-identified application, the filing date that determines Patent Term Adjustment is the filing date of the most recent CPA.

Applicant will be able to obtain more detailed information by accessing the Patent Application Information Retrieval (PAIR) system (http://pair.uspto.gov).

Any questions regarding the Patent Term Extension or Adjustment determination should be directed to the Office of Patent Legal Administration at (703) 305-1383. Questions relating to issue and publication fee payments should be directed to the Customer Service Center of the Office of Patent Publication at (703) 305-8283.

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	Application No.	Applicant(s)	12.0		
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Notice of Allowability	Examin r	Art Unit			
	Kenneth J. Ramsey	2879			
The MAILING DATE of this communication apperall claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.3131. This communication is responsive to election made 11/6/2022. The allowed claim(s) is/are 1-19.	(OR REMAINS) CLOSED in the or other appropriate communic GHTS. This application is subjured MPEP 1308.	is application. If not include cation will be mailed in due	ed course. THIS		
3. $oxed{\boxtimes}$ The drawings filed on <u>09 February 2002</u> are accepted by the					
 Acknowledgment is made of a claim for foreign priority un a) ☐ All b) ☐ Some* c) ☐ None of the: 	der 35 U.S.C. § 119(a)-(d) or (i).			
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3. Copies of the certified copies of the priority doc	cuments have been received in	this national stage applica	ition from the		
International Bureau (PCT Rule 17.2(a)).					
* Certified copies not received: 5. Acknowledgment is made of a claim for domestic priority us reference was included in the first sentence of the specification. (a) The translation of the foreign language provisional a claim for domestic priority us in the first sentence of the specification or in an Application.	ition or in an Application Data S pplication has been received. nder 35 U.S.C. §§ 120 and/or 1	Sheet. 37 CFR 1.78.			
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(b) ☐ including changes required by the proposed drawing correction filed, which has been approved by the Examiner.					
(c) ☐ including changes required by the attached Examiner's	s Amendment / Comment or in	the Office action of Paper	No		
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1⊠ Notice of References Cited (PTO-892)	-	al Patent Application (PTO	,		
2 Notice of Draftperson's Patent Drawing Review (PTO-948)	-	nary (PTO-413), Paper No.	·		
3 Information Disclosure Statements (PTO-1449 or PTO/SB/08 Paper No	7⊠ Examiner's Ame	7⊠ Examiner's Amendment/Comment			
4 Examiner's Comment Regarding Requirement for Deposit of Biological Material	8⊠ Examiner's Stat 9⊡ Other	ement of Reasons for Allov	vance		
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Art Unit: 2879

EXAMINER'S AMENDMENT

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Jason Z. Lin on January 26, 2004.

In regard to the changes below, it is also submitted that since the meaning of the term "photoconductive" is apparent from the context of the text, no change of claim scope is made below. In any event, at most, the change broadens the claims to reflect the correct scope of the claims to which applicants are entitled.

Applicants agent agreed to fax a paper indicating each occurence of "photoconductive" that appeared in the application so that the examiner could make the required changes by examiner's amendment. The examiner did not intend that the requirements of 37 C.F.R. 1.126 apply since the amendments were to be done by examiner's amendment merely using the fax as a guide since rule 126 does not apply to examiner' amendments. However, since the faxed changes comply with the rule for formal amendments, it was decided to paste the proposed changes directly into this examiner's amendment to avoid any error in the examiner's amendment.

Changes to the specification begin on page 3.

Changes to the claims begin on page 7.

Reasons for allowance appear on page 12.

AMENDMENTS TO THE SPECIFICATION:

Page 2, amend paragraph [0006] as:

[0006] This invention has been made to overcome the above-mentioned drawbacks of

conventional field emission displays. The primary object is to provide a fabrication

method for the cathode plate of a carbon nano tube field emission display. By combining

photolithography process and etching process, the method uses a photosensitive

photoconductive paste and an etchable dielectric material to fabricate the cathode plate of

a carbon nano tube field emission display.

Pages 2-3, amend paragraph [0007] as:

[0007] According to this invention, the fabrication method for the cathode plate of a

carbon nano tube field emission display comprises the preparation of a transparent

substrate and the fabrication of a cathode electrode layer, a dielectric layer, a gate layer,

and a CNT emission layer. During the fabrication, a transparent substrate having top and

bottom surfaces is first prepared. A layer of photosensitive photoconductive paste is

deposited on a surface of the transparent substrate. A pattern is then defined by a

photolithography process and sintered to finish a cathode electrode layer.

Page 3, amend paragraph [0008] as:

[0008] The whole surface of the cathode electrode layer is deposited with a layer of

ctchable dielectric material. A layer of photosensitive photoconductive gate material is

further deposited on the dielectric layer. Gate patterns are then printed by a

photolithography process and sintered to finish a gate electrode layer. The gate pattern is

used as a protecting film to etch a portion of the dielectric layer not covered by the protecting film in a photolithography process and finally a CNT emission layer is filled on the cathode electrode layer to form a cathode plate structure.

Page 7, amend paragraph [0028] as:

[0028] Referring to FIG. 3a, the fabrication process of the cathode electrode layer comprises the steps or preparing a transparent substrate 201 having top and bottom surfaces, depositing a layer of photosensitive photoconductive paste 301 on a surface of the transparent substrate 201, defining a pattern by photolithography process and sintering to form a cathode electrode layer 203. The photolithography process includes the definition of a pattern by a photo-mask 303 after pre-bake, and the steps of photo exposure 305 and development. FIG. 3b illustrates a cross sectional view of a pattern of the cathode electrode layer 203 after developing.

Page 7, amend paragraph [0029] as:

[0029] In the preferred embodiments of the present invention, the <u>photosensitive</u> photosenductive paste can be made by mixing conductive metal powder and resin with solvent and photosensitive emulsion. The conductive metal powder can be silver (Ag), nickel (Ni), or chromium (Cr). The resin can be trimethylpentanedial manaisobutyrate, acrylic resin, or methyl acrylate. The sintering time is about 30 minutes at a temperature between 480 °C to 560 °C in an air atmosphere. The transparent substrate is usually a glass substrate.

Page 8, amend paragraph [0031] as:

FIG. 5 illustrates the fabrication process for the gate electrode layer of the 100311 cathode plate in a carbon nano tube field emission display according to the invention. A layer of photosensitive photoconductive gate material 501 is deposited on the whole surface of the dielectric layer 205. After photolithography process and sintering, a gate pattern 207 is formed. In this embodiment, the dielectric layer is sintered to burn away the residual organic material in each layer before depositing the layer of photosensitive photoconductive gate material 501. The sintering time is about 30 minutes at a temperature between 480 °C to 540 °C in an air atmosphere. The photolithography process includes defining a pattern by a photo-mask 503 after pre-bake, photo exposure 505 and developing. FIG. 5b illustrates a cross sectional view of a pattern of the gate electrode layer 207 after the development.

Pages 11-12, amend paragraph [0043] as:

In summary, this invention uses photosensitive photosenductive paste and [0043] etchable dielectric material and combines photolithography process and etching process to fabricate the cathode plate of a carbon nano tube field emission display. It overcomes the drawback of conventional screen printing methods in which the resolution of the printed pattern is difficult to increase. The advantages of this invention also include simple fabrication process, uniform thickness of the film, and accurate printed patterns. Also, the distribution of the electric field is uniform and the alignment at the post-process is not difficult.

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Page 20, amend ABSTRACT as:

A method for fabricating the cathode plate of a carbon nano tube field emission

display uses a photosensitive photoconductive paste and etchable dielectric material to

fabricate the cathode plate. The method combines photolithography process and etching

process to fabricate a cathode electrode layer, a dielectric layer, a gate layer, and a carbon

nano tube emission layer. Packing this cathode plate structure with a conventional anode

plate together can form a carbon nano tube field emission array. The distribution of the

electric field is uniform and the alignment at post-process is made easy.

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AMENDMENTS TO THE CLAIMS:

1. (Currently Amended) A method for fabricating a cathode plate of a carbon nano tube

field emission display, said method comprising the steps of:

(a) preparing a transparent substrate;

(b) depositing a layer of photosensitive photoconductive paste on said transparent

substrate, patterning said layer of photosensitive photoconductive paste using a

photolithography process, and sintering to form a cathode electrode layer;

(c) depositing a layer of etchable dielectric material on said cathode electrode layer

and said transparent substrate;

(d) depositing a layer of photosensitive photoconductive gate material on said layer of

dielectric material, patterning said layer of photosensitive photoconductive gate

material using a photolithography process, and sintering to form a gate electrode

layer;

(c) using said gate electrode layer as a protecting film to pattern said layer of

dielectric material with a photolithography process to form field emission regions

above said cathode electrode layer, and

(f) filling said field emission regions with a carbon nano tube emission layer on said

cathode electrode layer.

2. (Currently Amended) The method for fabricating a cathode plate of a carbon nano

tube field emission display as claimed in claim 1, wherein said photosensitive

photoconductive paste in step (b) is made by mixing conductive metal powder and

resin with solvent and photosensitive emulsion.

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Page 8

3. (Currently Amended) The method for fabricating a cathode plate of a carbon nano tube field emission display as claimed in claim 1, wherein said photosensitive

photoconductive gate material in step (d) is made by mixing conductive metal powder

and resin with solvent and photosensitive emulsion.

4. (Original) The method for fabricating a cathode plate of a carbon nano tube field

emission display as claimed in claim 1, wherein said dielectric material in step (c) is

made by mixing dielectric powder chosen from the group of SiO2, Na2O, Li2O, PbO2

and BO₂, and resin with solvent.

5. (Original) The method for fabricating a cathode plate of a carbon nano tube field

emission display as claimed in claim 1, wherein sintering in step (b) is processed for

about 30 minutes at a temperature in the range of 480 °C to 560 °C in an air

atmosphere.

6. (Original) The method for fabricating a cathode plate of a carbon nano tube field

emission display as claimed in claim 1, wherein sintering in step (d) is processed for

about 30 minutes at a temperature in the range of 480 °C to 560 °C in an air

atmosphere.

7. (Original) The method for fabricating a cathode plate of a carbon nano tube field

emission display as claimed in claim 1, further comprising a step of sintering said

layer of dielectric material to burn away residual organic materials in each layer after

depositing said layer of etchable dielectric material in step (c).

8. (Original) The method for fabricating a cathode plate of a carbon nano tube field

emission display as claimed in claim 7, wherein said sintering step in step (c) is processed for about 30 minutes at a temperature in the range of 480 °C to 540 °C in an air atmosphere.

- 9. (Original) The method for fabricating a cathode plate of a carbon nano tube field emission display as claimed in claim 1, wherein step (f) further includes a step of sintering to burn away residual organic materials in each layer before filling said field emission regions with a carbon nano tube emission layer.
- 10. (Original) The method for fabricating a cathode plate of a carbon nano tube field emission display as claimed in claim 1, wherein each photolithography process includes the steps of defining a pattern by a photo-mask after pre-bake, photo exposure and developing.
- 11. (Original) The method for fabricating a cathode plate of a carbon nano tube field emission display as claimed in claim 1, wherein said carbon nano tube emission layer in step (f) is filled on said cathode electrode layer by an electrical deposition method.
- 12. (Original) The method for fabricating a cathode plate of a carbon nano tube field emission display as claimed in claim 11, wherein said carbon nano tube paste is made by mixing a dispersant with carbon nano tube powder of 3-50 weight percentage and solvent.
- 13. (Original) The method for fabricating a cathode plate of a carbon nano tube field emission display as claimed in claim 1, wherein said carbon nano tube emission layer in step (f) is filled by an electrical deposition method comprising the steps of forming

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a photoresist layer above said gate electrode layer, depositing a carbon nano tube paste into said field emission regions electrically, and sintering to remove residual organic materials in each layer of said cathode plate in a high temperature oven.

- 14. (Original) The method for fabricating a cathode plate of a carbon nano tube field emission display as claimed in claim 13, wherein said sintering step after depositing said carbon nano tube paste into said field emission regions is processed for about 30 minutes at a temperature in the range of 480 °C to 500 °C in a nitrogen atmosphere.
- 15. (Original) The method for fabricating a cathode plate of a carbon nano tube field emission display as claimed in claim 1, wherein said carbon nano tube emission layer in step (f) is filled on said cathode electrode layer by a photolithography method.
- 16. (Original) The method for fabricating a cathode plate of a carbon nano tube field emission display as claimed in claim 15, wherein said photosensitive carbon nano tube paste is made by mixing photoresist with carbon nano tube powder of 5-30 weight percentage and silver powder of 5-30 weight percentage.
- 17. (Original) The method for fabricating a cathode plate of a carbon nano tube field emission display as claimed in claim 1, wherein said carbon nano tube emission layer in step (f) is filled by a photolithography method comprising the steps of depositing a layer of photosensitive carbon nano tube paste on the surface of said cathode plate, defining a pattern for said carbon nano tube emission layer by alignment and exposure, and sintering to remove residual organic materials in each layer of said cathode plate in a high temperature oven.

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- 18. (Original) The method for fabricating a cathode plate of a carbon nano tube field emission display as claimed in claim 17, wherein said sintering step after depositing said carbon nano tube paste into said field emission regions is processed for about 30 minutes at a temperature in the range of 480 °C to 500 °C in a nitrogen atmosphere.
- 19. (Currently Amended) A method for fabricating a cathode plate of a carbon nano tube field emission display, said method comprising the steps of:
 - (a) providing a transparent substrate;
 - (b) depositing a layer of <u>photosensitive</u> photoconductive paste on said transparent substrate, patterning said layer of <u>photosensitive</u> photoconductive paste using a photolithography process, and sintering to form a cathode electrode layer;
 - (c) printing a carbon nano tube emission layer on said cathode electrode layer by a screen printing method;
 - (d) depositing a layer of etchable dielectric material on said carbon nano tube emission layer, said cathode electrode layer and said transparent substrate;
 - (e) depositing a layer of <u>photosensitive</u> <u>photoconductive</u> gate material on said layer of dielectric material, patterning said layer of <u>photosensitive</u> <u>photoconductive</u> gate material using a photolithography process, and sintering to form a gate electrode layer; and
 - (f) using said gate electrode layer as a protecting film to etch said layer of dielectric material with a photolithography process and expose said carbon nano tube emission layer above said cathode electrode layer, and sintering to remove residual organic materials in each layer.

Claims 20-28 are canceled as being to an invention non-elected without traverse.

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REASONS FOR ALLOWANCE

The following is an examiner's statement of reasons for allowance: the prior art does not teach or suggest the method of claim 1, particularly the steps of depositing a layer of photo-sensitive gate material, patterning the layer of gate material using a photolithography process, sintering the gate material to form a gate electrode, and using the gate electrode layer as a protecting film to pattern the layer of dielectric material using a photolithography process to form field emission regions above the cathode layer; and filling the field emission regions with a carbon nano tube emission layer; nor the process of claim 19, particularly the steps of printing a carbon nanotube emission layer on the cathode electrode layer by screen printing, depositing a layer of photosensitive gate material, patterning the layer of gate material using a photolithography process, sintering the gate material to form a gate electrode, and using the gate electrode layer as a protecting film to etch the layer of dielectric material. Claims 2-18 depend from claim 1 and are thus allowed.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Directions for Responses

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Kenneth J. Ramsey whose telephone number is (571) 272-2462. The examiner can normally be reached on M-F from 9 to 5.

KENNETH J. RAMSEY PRIMARY EXAMINER